Ordering number : ENN7035

P-Channel Silicon MOSFET

EC4302C

Small Signal Switch, Interface Applications

Features

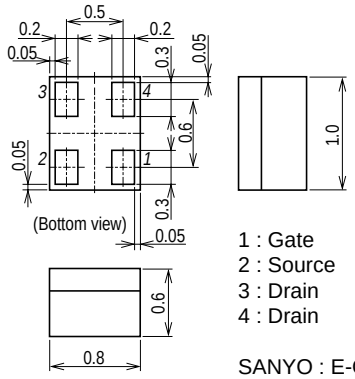
- Low ON-resistance.
- Ultrahigh-speed switching.
- 2.5V drive.

Package Dimensions

unit : mm

2197

[EC4302C]



1 : Gate
2 : Source
3 : Drain
4 : Drain

SANYO : E-CSP1008-4

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V_{DSS}		−50	V
Gate-to-Source Voltage	V_{GSS}		±10	V
Drain Current (DC)	I_D		−0.07	A
Drain Current (Pulse)	I_{DP}	PW≤10μs, duty cycle≤1%	−0.28	A
Allowable Power Dissipation	P_D		0.15	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		−55 to +150	°C

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	I_D=−1mA, V_{GS}=0	−50			V
Zero-Gate Voltage Drain Current	I_{DSS}	V_{DS}=−50V, V_{GS}=0			−10	μA
Gate-to-Source Leakage Current	I_{GSS}	V_{GS}=±8V, V_{DS}=0			±10	μA
Cutoff Voltage	$V_{GS}(off)$	V_{DS}=−10V, I_D=−100μA	−0.4		−1.4	V
Forward Transfer Admittance	$\|yfs\|$	V_{DS}=−10V, I_D=−40mA	70	100		mS
Static Drain-to-Source On-State Resistance	$R_{DS}(on)1$	I_D=−40mA, V_{GS}=−4V		18	23	Ω
	$R_{DS}(on)2$	I_D=−20mA, V_{GS}=−2.5V		20	28	Ω
	$R_{DS}(on)3$	I_D=−5mA, V_{GS}=−1.5V		30	60	Ω

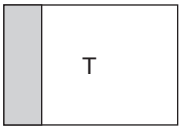
Continued on next page.

SANYO Electric Co.,Ltd. Semiconductor Company
TOKYO OFFICE Tokyo Bldg., 1-10, 1 Chome, Ueno, Taito-ku, TOKYO, 110-8534 JAPAN

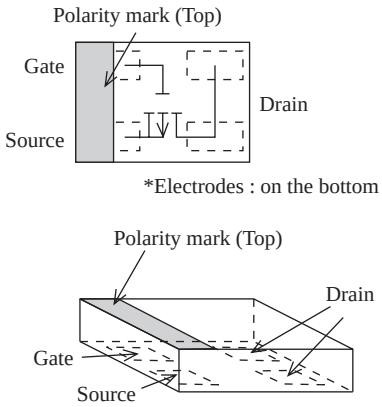
Continued from preceding page.

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Input Capacitance	Ciss	V_{DS}=–10V, f=1MHz		7.4		pF
Output Capacitance	Coss	V_{DS}=–10V, f=1MHz		4.2		pF
Reverse Transfer Capacitance	Crss	V_{DS}=–10V, f=1MHz		1.3		pF
Turn-ON Delay Time	t_{d}(on)	See specified Test Circuit.		20		ns
Rise Time	t_{r}	See specified Test Circuit.		35		ns
Turn-OFF Delay Time	t_{d}(off)	See specified Test Circuit.		160		ns
Fall Time	t_{f}	See specified Test Circuit.		150		ns
Total Gate Charge	Qg	V_{DS}=–10V, V_{GS}=–10V, I_{D}=–70mA		1.40		nC
Gate-to-Source Charge	Qgs	V_{DS}=–10V, V_{GS}=–10V, I_{D}=–70mA		0.16		nC
Gate-to-Drain “Miller” Charge	Qgd	V_{DS}=–10V, V_{GS}=–10V, I_{D}=–70mA		0.23		nC
Diode Forward Voltage	V_{SD}	I_{S}=–70mA, V_{GS}=0		–0.9	–1.2	V

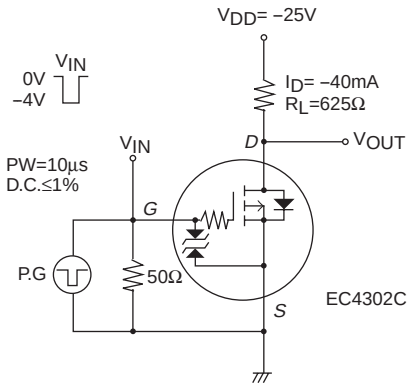
Type No. Indication(Top view)

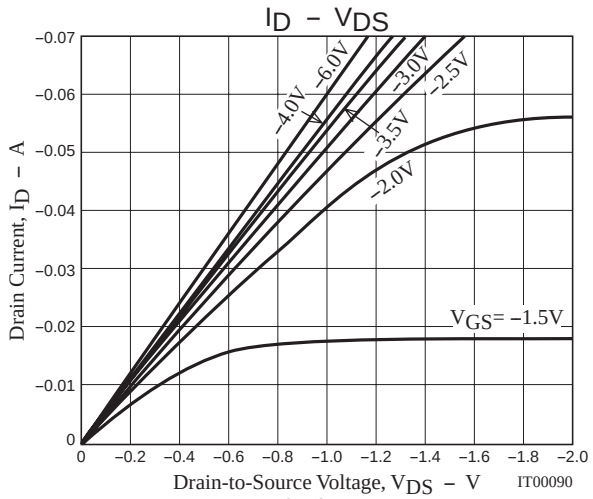


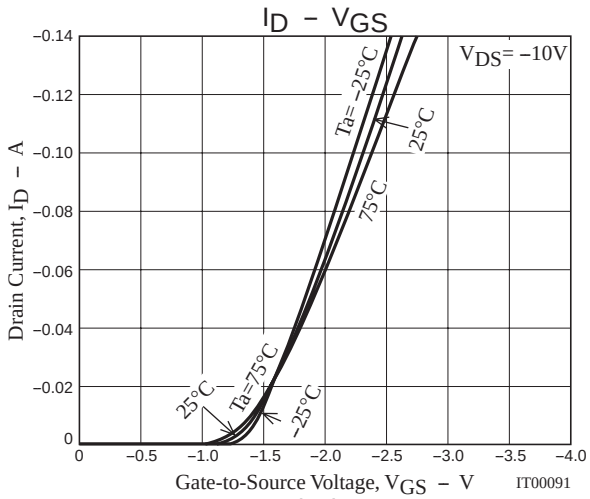
Electrical Connection(Top view)

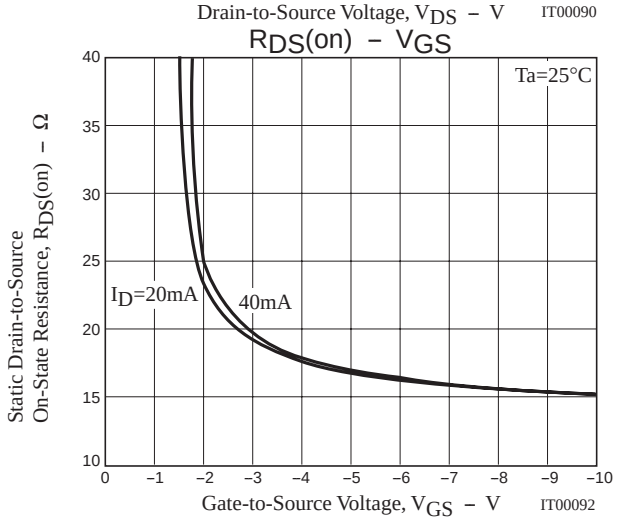


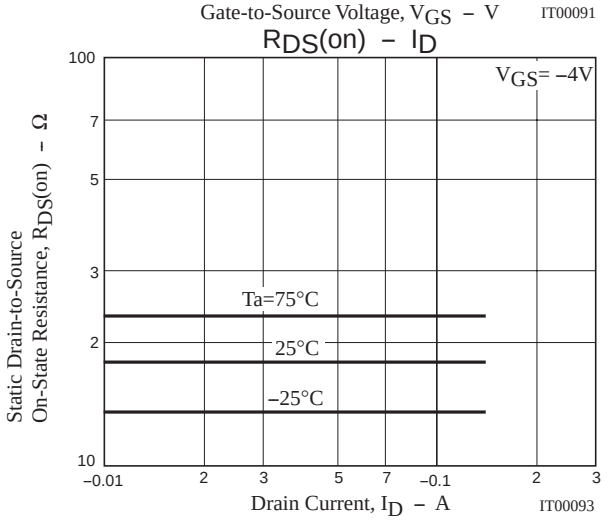
Switching Time Test Circuit

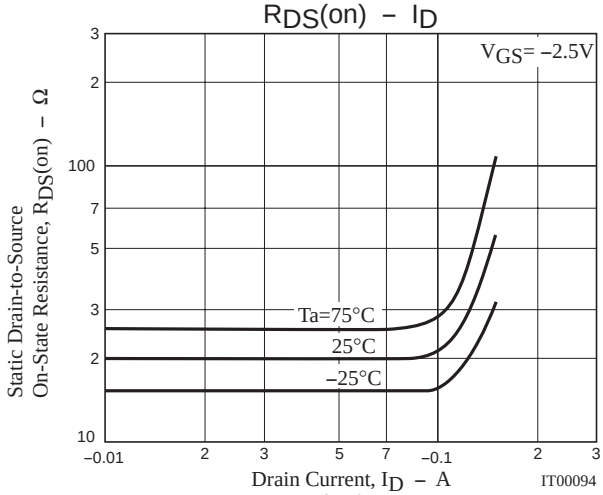


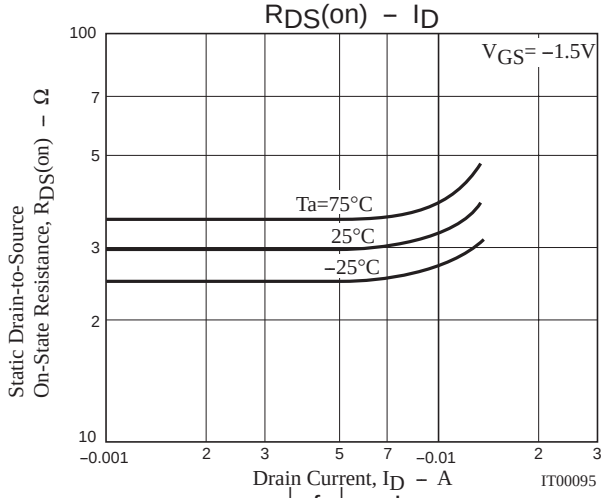


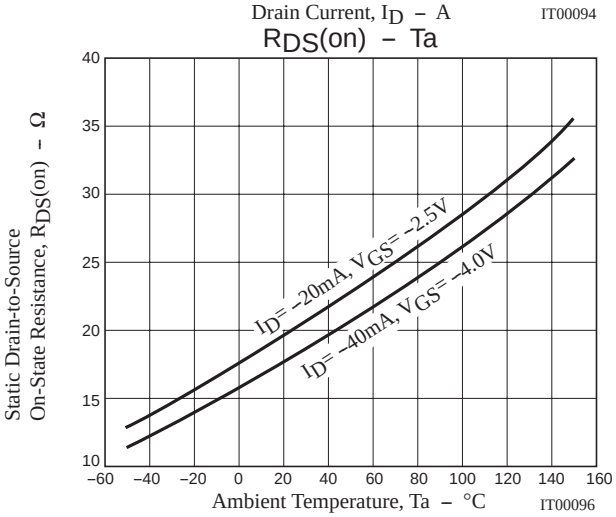


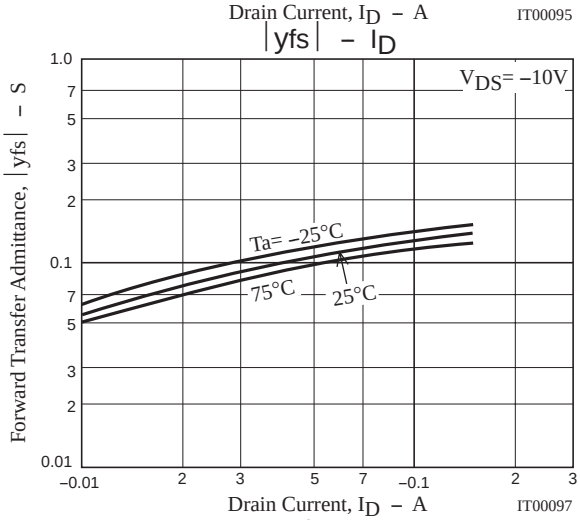


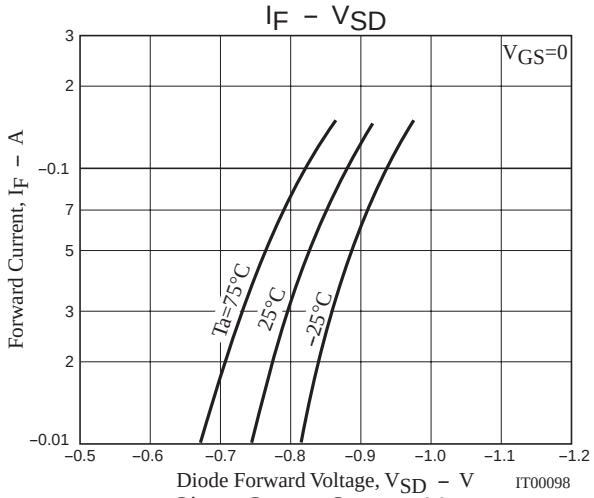


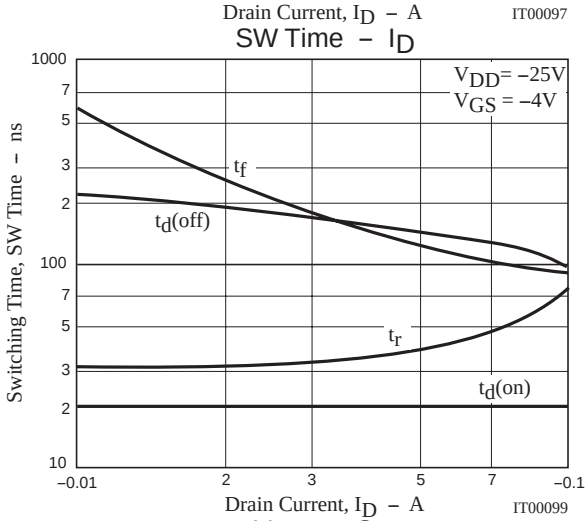

RDS(on) – ID
VGS= –2.5V
Ta=75°C
25°C
–25°C
Static Drain-to-Source On-State Resistance, RDS(on) – Ω
Drain Current, ID – A
IT00094

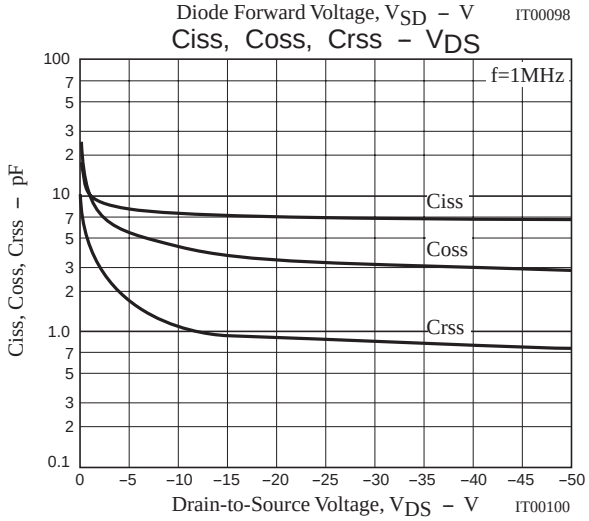

RDS(on) – ID
VGS= –1.5V
Ta=75°C
25°C
–25°C
Static Drain-to-Source On-State Resistance, RDS(on) – Ω
Drain Current, ID – A
IT00095

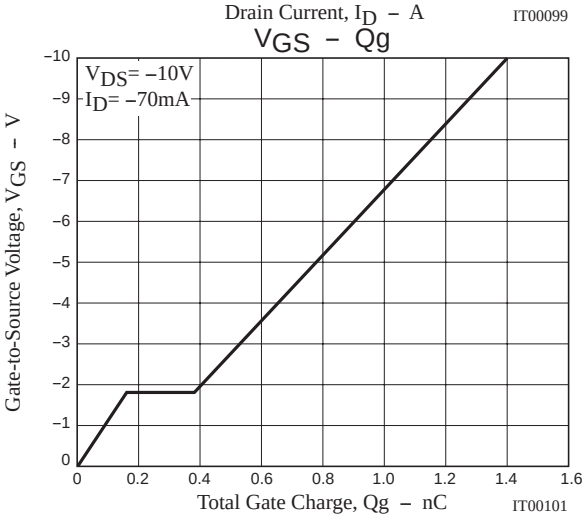

RDS(on) – Ta
ID= –20mA, VGS= –2.5V
ID= –40mA, VGS= –4.0V
Static Drain-to-Source On-State Resistance, RDS(on) – Ω
Ambient Temperature, Ta – °C
IT00096

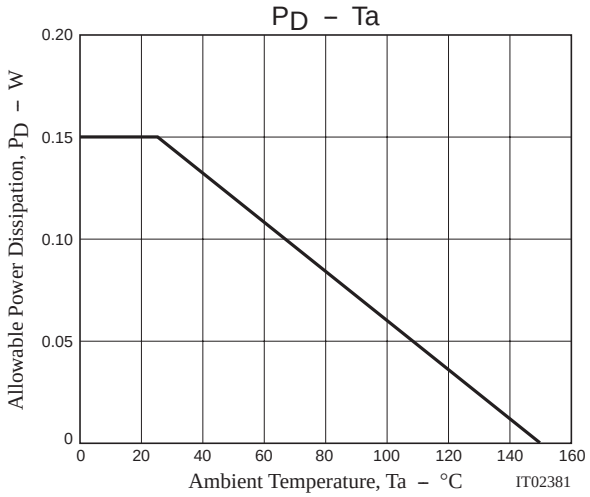

|yfs| – ID
VDS= –10V
Ta= –25°C
75°C
25°C
Forward Transfer Admittance, |yfs| – S
Drain Current, ID – A
IT00097


IF – VSD
VGS=0
Ta=75°C
25°C
–25°C
Forward Current, IF – A
Diode Forward Voltage, VSD – V
IT00098


SW Time – ID
VDD= –25V
VGS = –4V
tf
td(off)
tr
td(on)
Switching Time, SW Time – ns
Drain Current, ID – A
IT00099


Ciss, Coss, Crss – VDS
f=1MHz
Ciss
Coss
Crss
Ciss, Coss, Crss – pF
Drain-to-Source Voltage, VDS – V
IT00100


VGS – Qg
VDS= –10V
ID= –70mA
Gate-to-Source Voltage, VGS – V
Total Gate Charge, Qg – nC
IT00101



Note on usage : Since the EC4302C is designed for high-speed switching applications, please avoid using this device in the vicinity of highly charged objects.